

4V Drive Nch MOSFET

RSD150N06

●Structure

Silicon N-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.

●Applications

Switching

●Packaging specifications

| | | |
|------|------------------------------|------|
| Type | Package | CPT3 |
| | Code | TL |
| | Basic ordering unit (pieces) | 2500 |

●Absolute maximum ratings (Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|------------------------------|------------|-------------|------------|
| Drain-source voltage | V_{DSS} | 60 | V |
| Gate-source voltage | V_{GSS} | ± 20 | V |
| Drain current | Continuous | I_D | ± 15 A |
| | Pulsed | I_{DP} *1 | ± 30 A |
| Source current (Body Diode) | Continuous | I_S | 15 A |
| | Pulsed | I_{SP} *1 | 30 A |
| Power dissipation | P_D *2 | 20 | W |
| Channel temperature | T_{ch} | 150 | °C |
| Range of storage temperature | T_{stg} | -55 to +150 | °C |

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

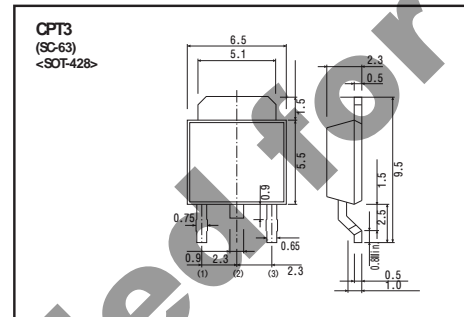
*2 $T_c = 25^\circ C$

●Thermal resistance

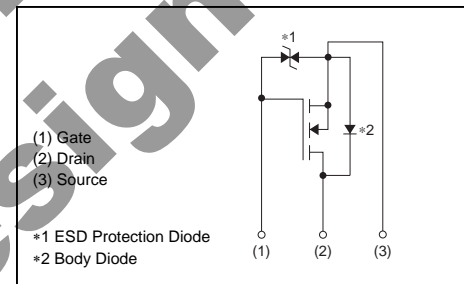
| Parameter | Symbol | Limits | Unit |
|-----------------|------------------|--------|--------|
| Channel to Case | $R_{th(ch-c)}$ * | 6.25 | °C / W |

* $T_c = 25^\circ C$

●Dimensions (Unit : mm)



●Inner circuit



*1 ESD Protection Diode
*2 Body Diode

●Electrical characteristics (T_a=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|-----------------------|------|------|------|------|--|
| Gate-source leakage | I _{GSS} | - | - | ±10 | μA | V _{GS} =±20V, V _{DS} =0V |
| Drain-source breakdown voltage | V _{(BR)DSS} | 60 | - | - | V | I _D =1mA, V _{GS} =0V |
| Zero gate voltage drain current | I _{DSS} | - | - | 1 | μA | V _{DS} =60V, V _{GS} =0V |
| Gate threshold voltage | V _{GS(th)} | 1.0 | - | 3.0 | V | V _{DS} =10V, I _D =1mA |
| Static drain-source on-state resistance | R _{DS(on)} * | - | 28 | 40 | mΩ | I _D =15A, V _{GS} =10V |
| | | - | 33 | 47 | | I _D =15A, V _{GS} =4.5V |
| | | - | 36 | 51 | | I _D =15A, V _{GS} =4.0V |
| Forward transfer admittance | Y _{fs} * | 7 | - | - | S | I _D =15A, V _{DS} =10V |
| Input capacitance | C _{iss} | - | 930 | - | pF | V _{DS} =10V |
| Output capacitance | C _{oss} | - | 200 | - | pF | V _{GS} =0V |
| Reverse transfer capacitance | C _{rss} | - | 80 | - | pF | f=1MHz |
| Turn-on delay time | t _{d(on)} * | - | 10 | - | ns | I _D =7.5A, V _{DD} =30V |
| Rise time | t _r * | - | 30 | - | ns | V _{GS} =10V |
| Turn-off delay time | t _{d(off)} * | - | 45 | - | ns | R _L =4.0Ω |
| Fall time | t _f * | - | 15 | - | ns | R _G =10Ω |
| Total gate charge | Q _g * | - | 18.0 | - | nC | V _{DD} =30V |
| Gate-source charge | Q _{gs} * | - | 3.2 | - | nC | I _D =15A, |
| Gate-drain charge | Q _{gd} * | - | 3.8 | - | nC | V _{GS} =10V |

*Pulsed

●Body diode characteristics (Source-Drain) (T_a = 25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-----------------|-------------------|------|------|------|------|--|
| Forward Voltage | V _{SD} * | - | - | 1.2 | V | I _s =15A, V _{GS} =0V |

*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (I)

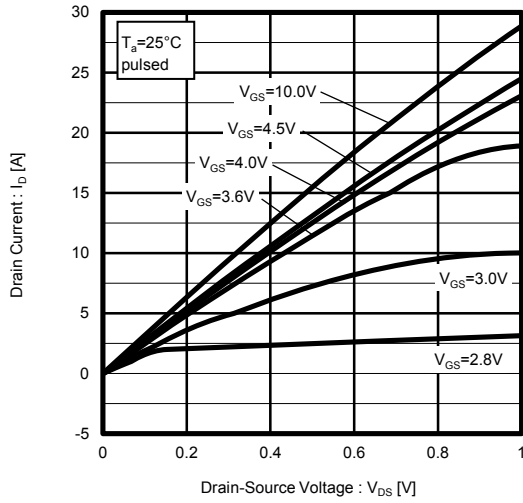


Fig.2 Typical Output Characteristics (II)

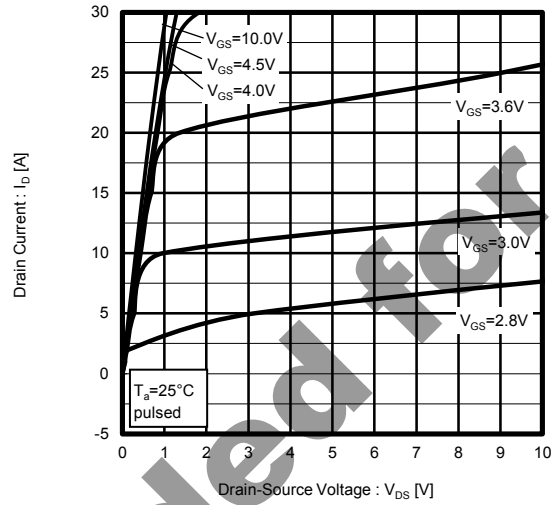


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

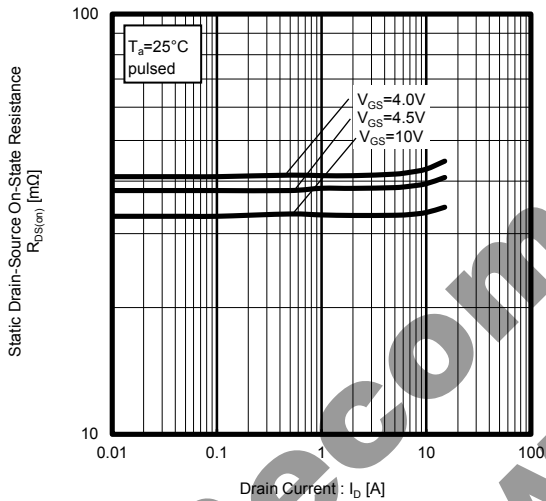


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

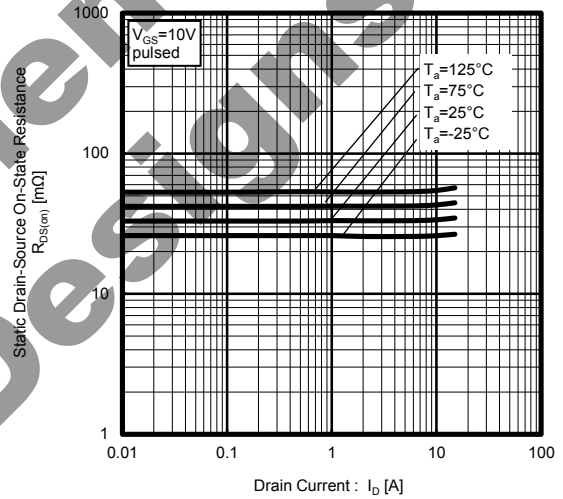


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

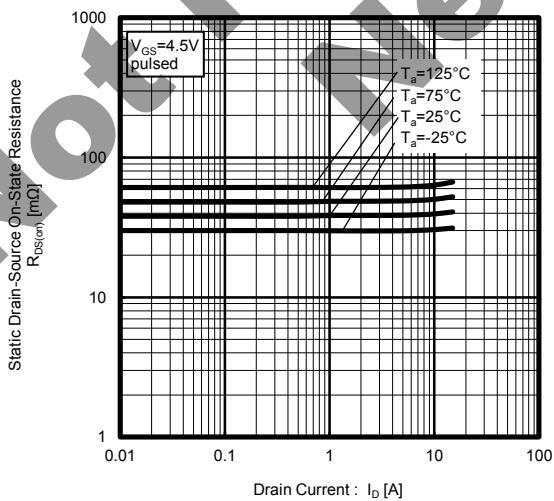


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

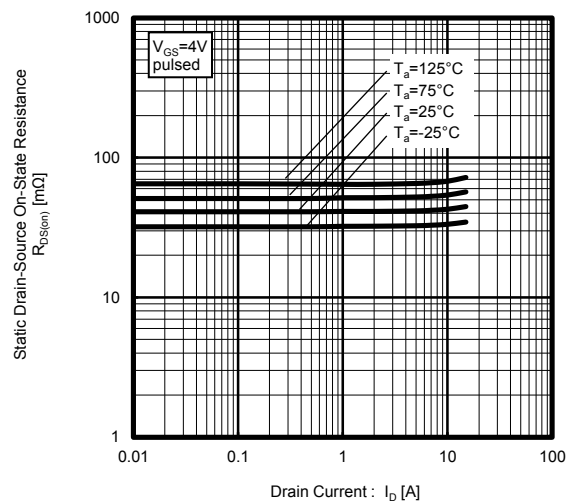


Fig.7 Forward Transfer Admittance vs. Drain Current

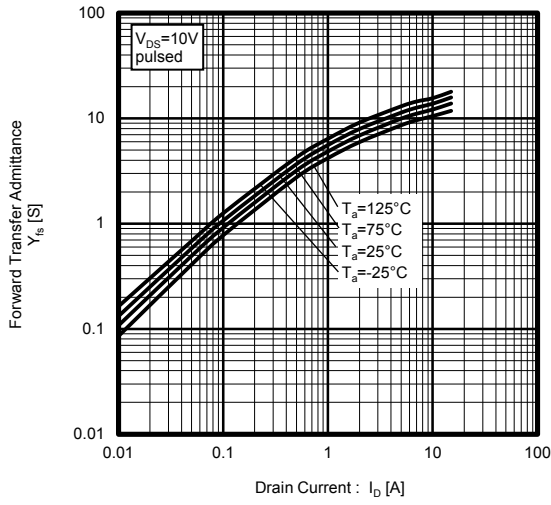


Fig.8 Typical Transfer Characteristics

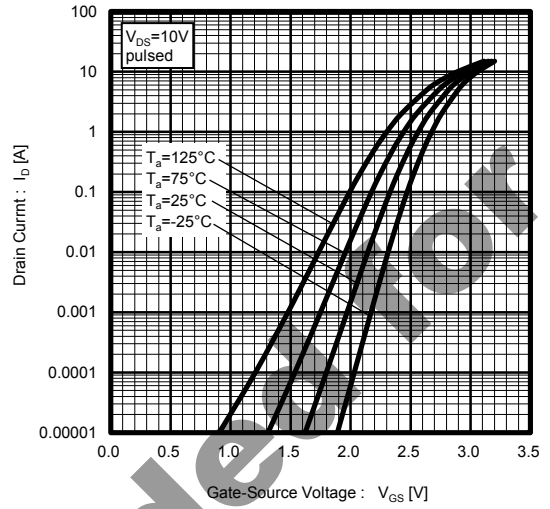


Fig.9 Source Current vs. Source-Drain Voltage

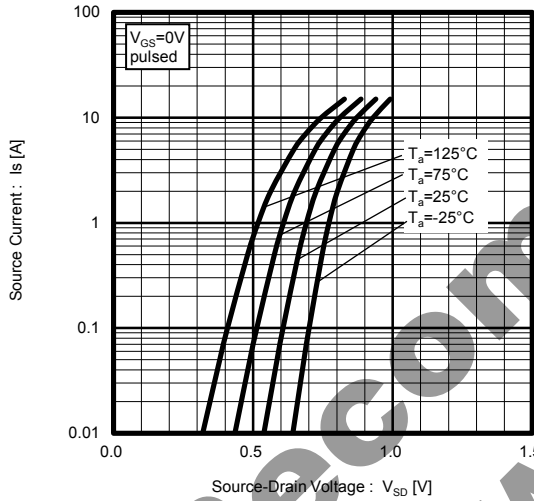


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

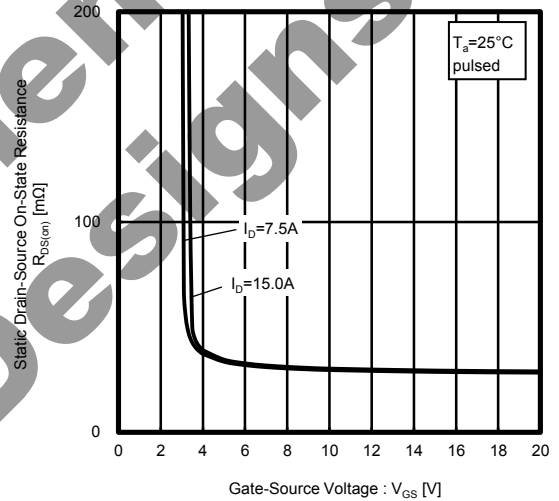


Fig.11 Switching Characteristics

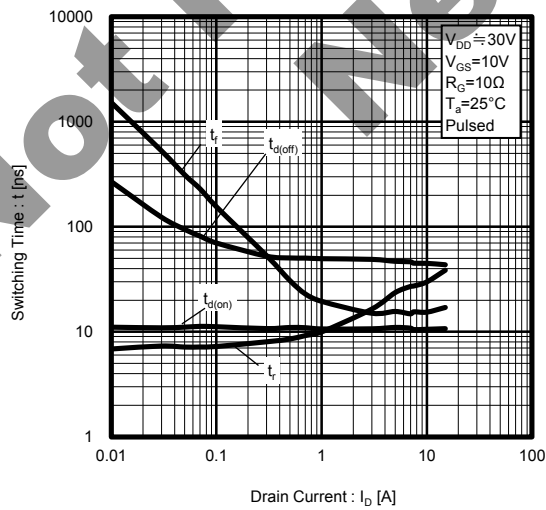


Fig.12 Dynamic Input Characteristics

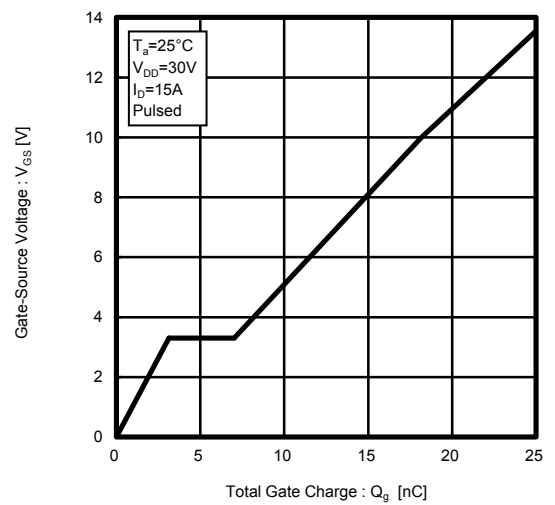


Fig.13 Typical Capacitance vs. Drain-Source Voltage

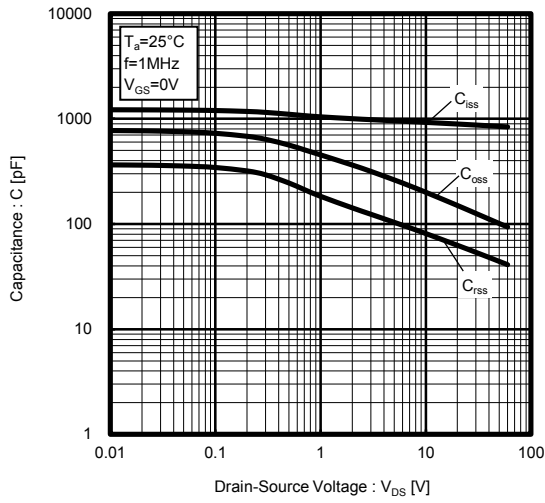


Fig.14 Maximum Safe Operating Area

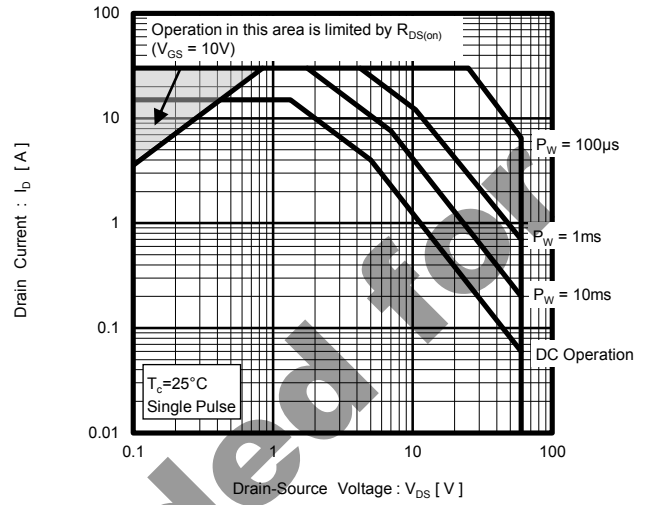
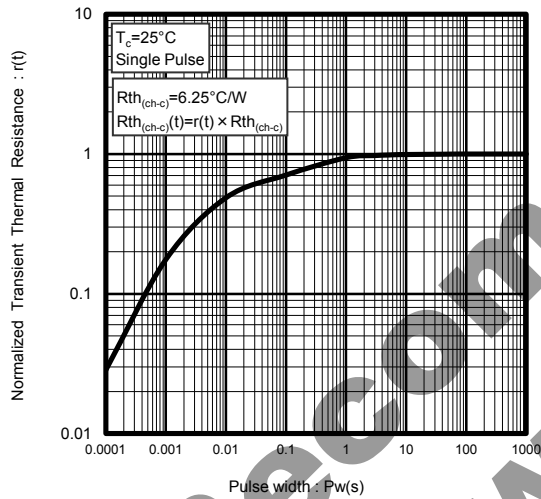


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



Not Recommended for New Designs

● Measurement circuits

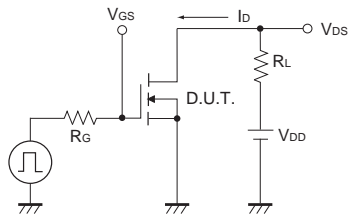


Fig.1-1 Switching Time Measurement Circuit

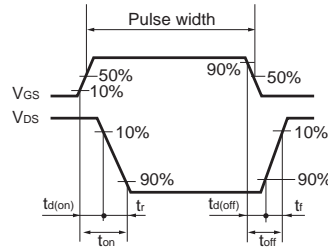


Fig.1-2 Switching Waveforms

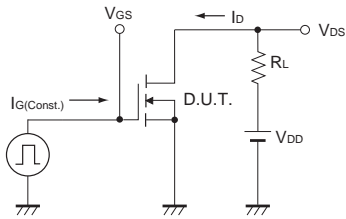


Fig.2-1 Gate Charge Measurement Circuit

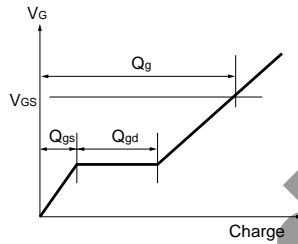


Fig.2-2 Gate Charge Waveform

Not Recommended for New Designs

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